

TENTATIVE

Features and Applications

- Low ON-state resistance.
- 4V drive.

Absolute Maximum Ratings / Ta=25°C

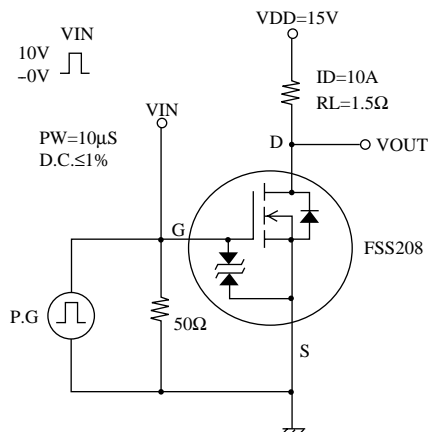
			unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current(DC)	ID	10	A
Drain Current(Pulse)	IDP	PW≤10μs,duty cycle≤1%	52 A
Allowable power Dissipation	PD	Mounted on ceramic board(1000mm ² × 0.8mm)	2 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics / Ta=25°C

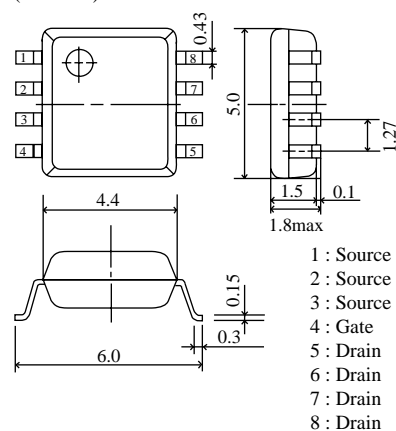
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	30			V
Zero Gate Voltage Drain Current	IDSS	VDS=30V , VGS=0			10	μA
Gate to Source Leakage Current	IGSS	VGS=±16V , VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V , ID=1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	VDS=10V , ID=10A	16	24		S
Static Drain to Source on State Resistance	RDS(on)1	ID=10A , VGS=10V		9.5	12.5	mΩ
	RDS(on)2	ID=4A , VGS=4V		15	20	mΩ
Input Capacitance	Ciss	VDS=10V , f=1MHz		1700		pF
Output Capacitance	Coss	VDS=10V , f=1MHz		920		pF
Reverse Transfer Capacitance	Crss	VDS=10V , f=1MHz		420		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit		20		ns
Rise Time	tr			360		ns
Turn-off Delay Time	td(off)			230		ns
Fall Time	tf			220		ns
Total Gate Charge	Qg	VDS=10V , VGS=10V , ID=10A		55		nC
Gate Source Charge	Qgs			11		nC
Gate Drain Charge	Qgd			14		nC
Diode Forward Voltage	VSD	IS=10A , VGS=0	1.0		1.2	V

Marking : S208

Switching Time Test Circuit



Package Dimensions SOP8(unit:mm)



Specifications and information herein are subject to change without notice.

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